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With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Dual P-Channel 1.8-V (G-S) MOSFET

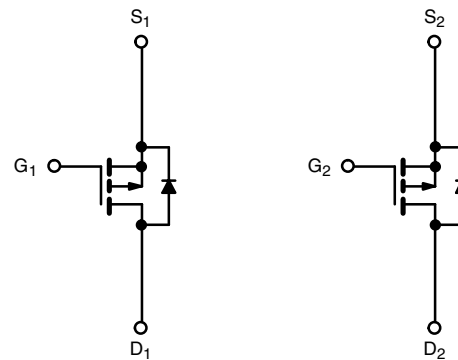
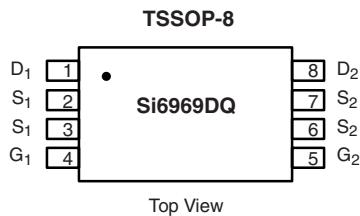
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.034 at $V_{GS} = - 4.5$ V	± 4.6
	0.050 at $V_{GS} = - 2.5$ V	± 3.8
	0.075 at $V_{GS} = - 1.8$ V	± 3.0

FEATURES

- Halogen-free
- TrenchFET[®] Power MOSFETs: 1.8 V Rated



RoHS
COMPLIANT



Ordering Information: Si6969DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	- 12	V	
Gate-Source Voltage	V_{GS}	± 8		
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	I_D	$T_A = 25$ °C	± 4.6	A
		$T_A = 70$ °C	± 3.8	
Pulsed Drain Current	I_{DM}	± 30		
Continuous Source Current (Diode Conduction) ^{a, b}	I_S	- 1.25		
Maximum Power Dissipation ^{a, b}	P_D	$T_A = 25$ °C	1.1	W
		$T_A = 70$ °C	0.72	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	110	°C/W	
		Steady State	115		

Notes:

a. Surface Mounted on FR4 board.

b. $t \leq 10$ s.

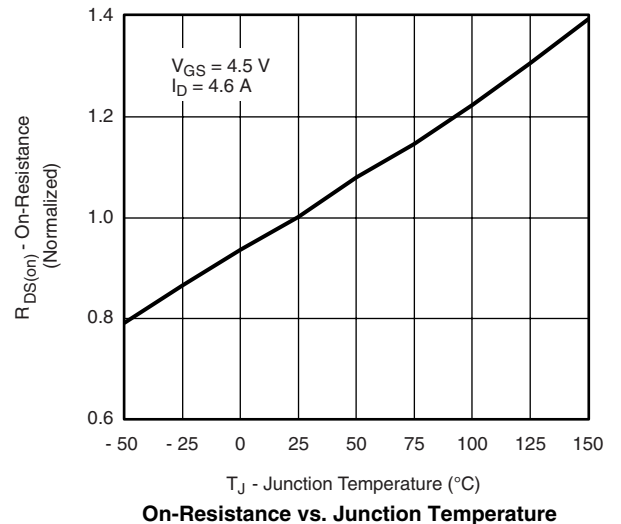
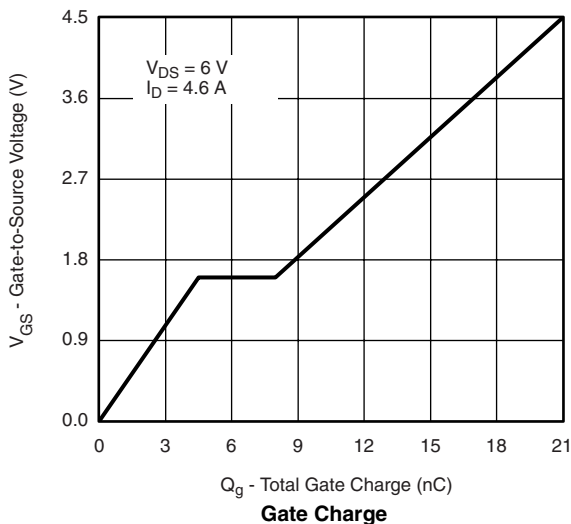
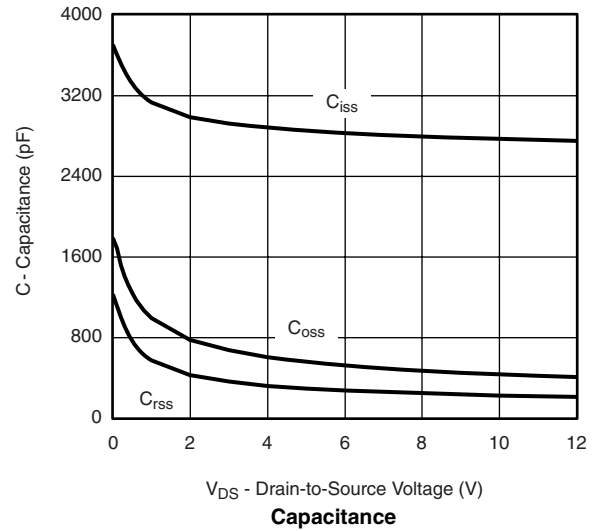
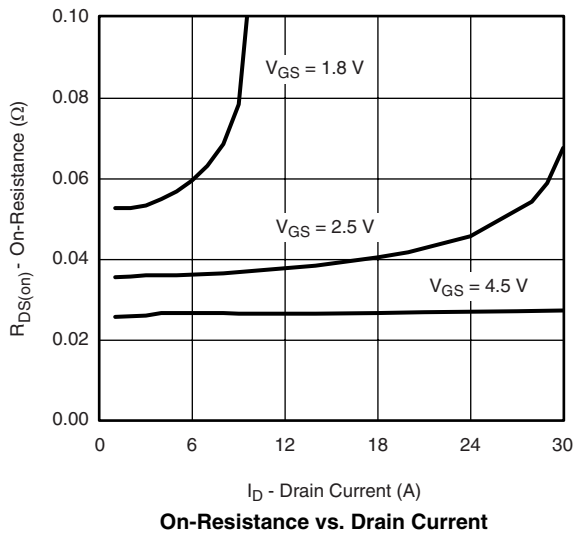
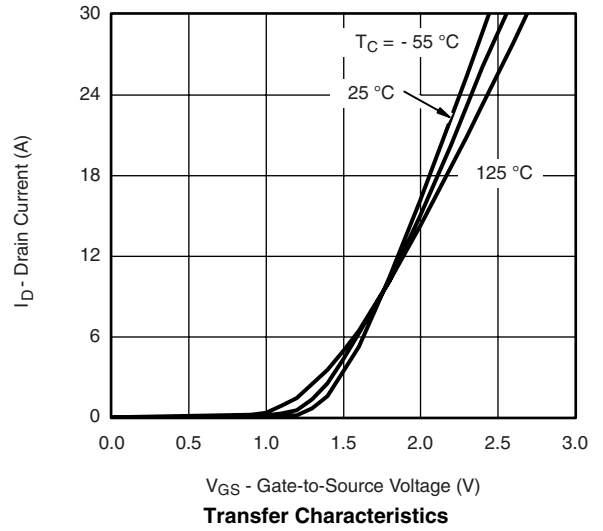
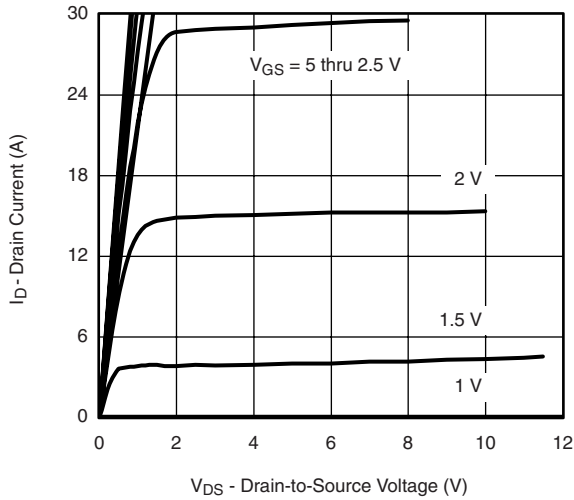
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.45			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -9.6\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -9.6\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			-25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -8\text{ V}, V_{GS} = -4.5\text{ V}$	-30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -4.6\text{ A}$		0.027	0.034	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -3.8\text{ A}$		0.037	0.050	
		$V_{GS} = -1.8\text{ V}, I_D = -3.0\text{ A}$		0.053	0.075	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -8\text{ V}, I_D = -4.6\text{ A}$		18		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.25\text{ A}, V_{GS} = 0\text{ V}$		-0.68	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -4.6\text{ A}$		21	40	nC
Gate-Source Charge	Q_{gs}		4.5			
Gate-Drain Charge	Q_{gd}		3.5			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 6\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		25	50	ns
Rise Time	t_r			35	60	
Turn-Off Delay Time	$t_{d(off)}$			80	150	
Fall Time	t_f			40	80	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.25\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		50	100	

Notes:

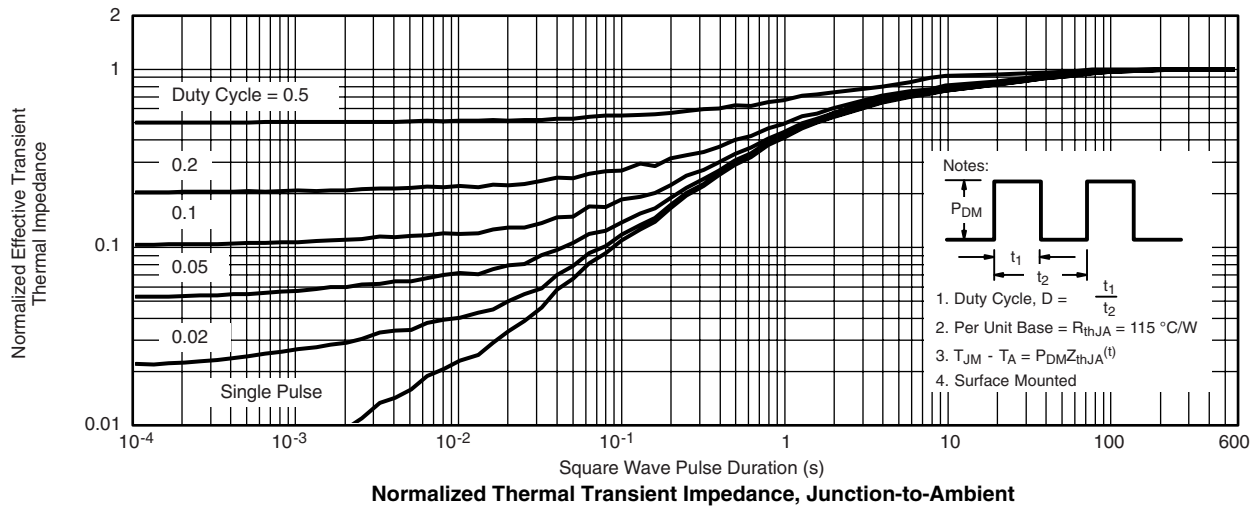
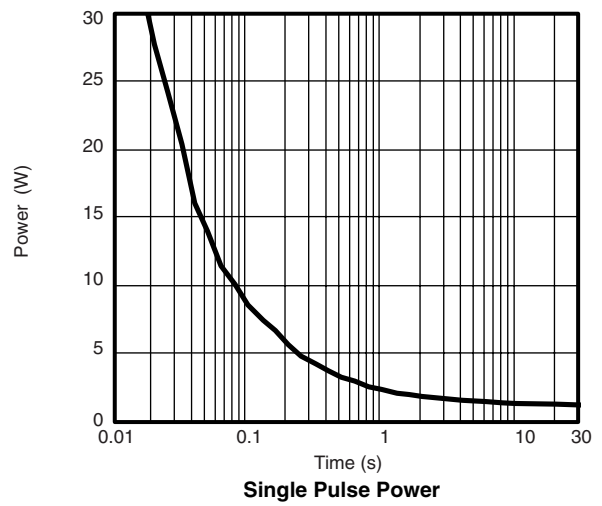
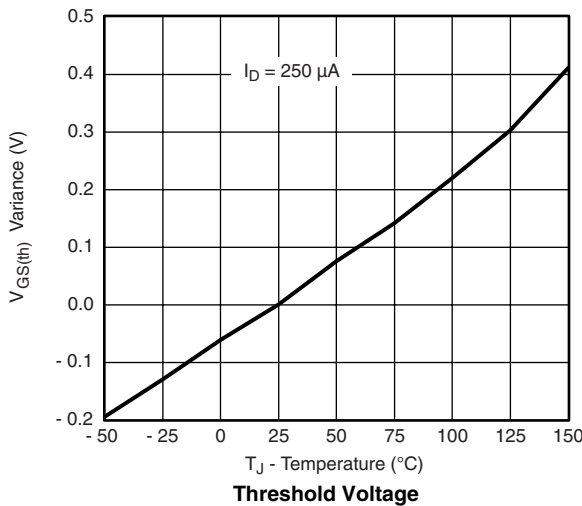
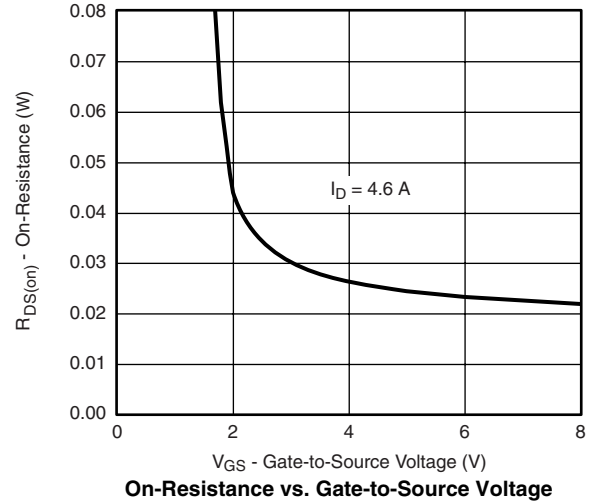
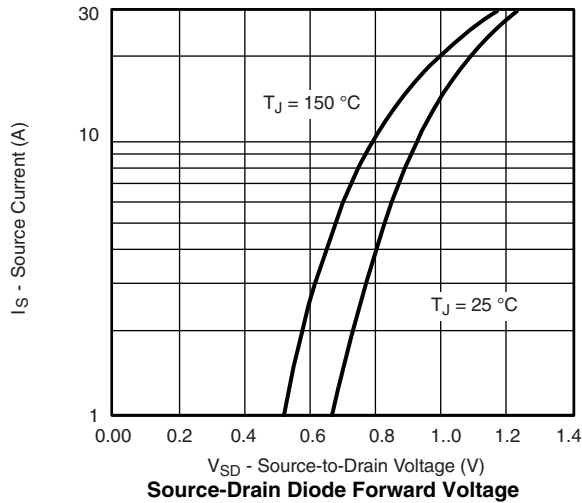
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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